

## COURSE DESCRIPTION – ACADEMIC YEAR 2024/2025

<b>Course title</b>	<b>Dispositivi Elettronici</b>
<b>Course code</b>	42409
<b>Scientific sector</b>	ING-INF/01
<b>Degree</b>	Bachelor in Electronics and Cyberphysical Systems (L-8)
<b>Semester</b>	1
<b>Year</b>	2
<b>Credits</b>	9
<b>Modular</b>	No
<b>Total lecturing hours</b>	54
<b>Total lab hours</b>	36
<b>Attendance</b>	Preferrable. Non-attending students should contact the lecturer at the start of the course to agree on the modalities of the independent study
<b>Prerequisites</b>	Mathematical Analysis I, Mathematical Analysis II, Physics I, Physics II
<b>Course page</b>	Teams
<b>Specific educational objectives</b>	The objective of this course is an understanding of the physics and operation of semiconductor devices. Specifically, understanding of the formation and behavior of metal-semiconductor contacts, basic knowledge of nanotechnology and microfabrication, understanding of operation and design of MOSFETs, bipolar transistor and JFET, and understanding of the operation of memories, optical devices and sensors.
<b>Lecturer</b>	Prof. Paolo Lugli Prof. Luisa Petti
<b>Contact</b>	paolo.lugli@unibz.it luisa.petti@unibz.it
<b>Scientific sector of lecturer</b>	ING/INF-01 – ELECTRONICS
<b>Teaching language</b>	Italian
<b>Office hours</b>	After consultation and agreement with lecturers
<b>Lecturing assistant (if any)</b>	
<b>Contact LA</b>	
<b>Office hours LA</b>	
<b>List of topics</b>	The topics covered include: <ul style="list-style-type: none"> <li>- Semiconducting materials.</li> <li>- Semiconductor fabrication and characterization techniques.</li> <li>- PN junctions and diodes.</li> <li>- Transistors (MOSFETs; MESFETs; heterojunction transistors)</li> <li>- Memories (DRAM; SRAM; Flash; resistive).</li> <li>- Sensors (physical; chemical; biological sensors).</li> <li>- Photonic devices (LEDs; lasers; photodiodes; solar cells).</li> <li>- Passive electronic components (antennas; batteries).</li> <li>- Internet-of-things and sensor networks.</li> </ul>
<b>Teaching format</b>	Frontal lectures, homeworks, exercises, and laboratories.

<b>Learning outcomes</b>	To be defined
<b>Assessment</b>	The exam will be in written form. One part will relate to the lecture topics, one other top the exercises. Students will have the choice to take 2 midterm exams (if negative, the students will have to take the final written exam including all covered topics).
<b>Assessment language</b>	Italian
<b>Evaluation criteria and criteria for awarding marks</b>	The assessment criteria will be the accuracy of the answers given in the written examination, with particular attention to the resolution procedure adopted and the formal correctness of the same.
<b>Required readings</b>	"Semiconductor Physics and Devices", Donald A. Neamen.
<b>Supplementary readings</b>	"Elettronica di Millman", Jacob Millman, Arvin Grabel, Pierangelo Terreni.